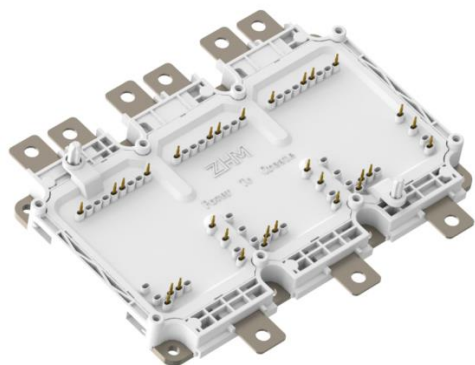


#### ➤ 产品外观 / Appearance

*Preliminary*



$V_{CES} = 750V$

$I_C = 820A$

#### ➤ 特性 / Features

- A. 沟槽型电场截止型 IGBT
- B. 低饱和电压
- C. 低开通损耗

- A. Field Stop Trench Gate IGBT
- B. Low  $V_{CESat}$
- C. Low Switching Loss

#### ➤ 用途 / Applications

- A. 电机传动
- B. 电动汽车应用
- C. 大功率变流器

- A. Motor Drives
- B. Electrical Vehicles Applications
- C. High Power Converters

#### ➤ 相关信息 / Related Information

条形码 / Barcode Code



二维码 / DMX – Code



公司地址：合肥市高新区创新大道与明珠大道交叉口 106 号 5 号楼 2 层 C 区、D 区。

Address: Area C and D, 2nd floor, Building 5, No. 106, Intersection of Innovation Avenue and Mingzhu Avenue, High-tech Zone, Hefei City.

# 6H820M08A1E

## IGBT, 逆变器 / IGBT, Inverter



### 最大额定值 / Maximum Rated Values

集电极-发射极电压 Collector-emitter voltage	$T_j = 25^\circ\text{C}$	$V_{CES}$	750	V
集电极电流 Implemented collector current		$I_{CN}$	820	A
连续集电极直流电流 Continuous DC collector current	$T_F = 80^\circ\text{C}, T_{j\max} = 175^\circ\text{C}$	$I_{C\text{nom}}$	450 <sup>1)</sup>	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\text{ms}$	$I_{CRM}$	1640	A
栅极-发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	$\pm 20$	V

### 特征值 / Characteristic Values

		Min.	Typ.	Max.			
集电极-发射极饱和电压 Collector-emitter saturation voltage	$I_C = 450\text{A}, V_{GE} = 15\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$V_{CE\text{sat}}$	1.30	1.60	V		
	$I_C = 820\text{A}, V_{GE} = 15\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$		1.40	1.45			
栅极阈值电压 Gate threshold voltage	$I_C = 9.6\text{mA}, V_{CE} = V_{GE}, T_j = 25^\circ\text{C}$	$V_{G\text{Eth}}$	5.0	5.8	6.8	V	
内部栅极电阻 Internal gate resistor	$T_j = 25^\circ\text{C}$	$R_{G\text{int}}$	0.67			$\Omega$	
输入电容/Input capacitance	$f = 1\text{MHz}, T_j = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{\text{ies}}$	60			nF	
反向传输电容 Reverse transfer capacitance		$C_{\text{res}}$	0.9			nF	
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 750\text{V}, V_{GE} = 0\text{V}, T_j = 25^\circ\text{C}$	$I_{CES}$			1.0	mA	
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = \pm 20\text{V}, T_j = 25^\circ\text{C}$	$I_{GES}$			400	nA	
开通延迟时间/Turn-on delay time	$I_C = 450\text{A}, V_{CE} = 400\text{V}$ $V_{GE} = +15\text{V}/-8\text{V}$ $R_G = 2\Omega$ Inductive Load	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$t_{d\text{on}}$	430		ns	
上升时间/Rise time		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$t_r$	260		ns	
开通损耗能量/Turn-on energy loss		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$E_{\text{on}}$	17.9		mJ	
关断延迟时间/Turn-off delay time		Turn-on( $T_j = 175^\circ\text{C}$ ): $di/dt = 1400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$t_{d\text{off}}$	675		ns
下降时间/Fall time		Turn-off( $T_j = 175^\circ\text{C}$ ): $dv/dt = 1400\text{V}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$t_f$	195		ns
关断损耗能量/Turn-off energy loss		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$E_{\text{off}}$	54.6		mJ	
短路数据/SC data		$V_{GE} \leq 15\text{V}, V_{CC} = 400\text{V}$ $t_p \leq 6\mu\text{s}, T_j = 25^\circ\text{C}$	$I_{SC}$	3900		A	
结 - 散热器热阻 / Thermal resistance, junction to cooling fluid 在开关状态下温度 Temperature under switching		per IGBT, cooling fluid = 50% water, $DV/DT = 10\text{dm}^3/\text{min}$	$R_{th\text{F}}$		0.12	K/W	
		$T_{j\text{op}}$	-40	150	$^\circ\text{C}$		

1) 通过特性/设计而不是测试来验证。

# 6H820M08A1E

二极管, 逆变器 / Diode, Inverter

负温度系数热敏电阻 / NTC-Thermistor



## 二极管, 逆变器 / Diode, Inverter

### 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_j = 25^\circ\text{C}$	$V_{RRM}$	750	V
连续正向直流电流 Continuous DC forward current		$I_F$	600	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1\text{ ms}$	$I_{FRM}$	1200	A

### 特征值 / Characteristic Values

		Min.	Typ.	Max.	
正向电压 Forward voltage	$I_F = 450\text{ A}, V_{GE} = 0\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$V_F$	1.55	1.90	V
	$I_F = 820\text{ A}, V_{GE} = 0\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$		1.40		
反向恢复峰值电流 Peak reverse recovery current	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$I_{RM}$	104		A
恢复电荷/Recovered charge	$I_F = 450\text{ A}, V_R = 400\text{ V}$ $V_{GE} = -8\text{ V}$ $-di_F/dt = 1800\text{ A}/\mu\text{s}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$Q_r$	11.2		$\mu\text{C}$
反向恢复损耗 Reverse recovery energy	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ $T_j = 175^\circ\text{C}$	$E_{rec}$	2.45		mJ
结 - 散热器热阻 / Thermal resistance, junction to cooling fluid	per Diode, cooling fluid = 50% water, DV/Dt = 10dm <sup>3</sup> /min	$R_{thJF}$		0.22	K/W
在开关状态下温度 Temperature under switching		$T_{j\text{op}}$	-40	150	$^\circ\text{C}$

## 负温度系数热敏电阻 / NTC-Thermistor

### 特征值 / Characteristic Values

		Min.	Typ.	Max.	
额定阻值/Rated resistance	$T_C = 25^\circ\text{C}$	$R_{25}$	5.00		k $\Omega$
阻值误差/Deviation of R100	$T_C = 100^\circ\text{C}, R_{100} = 465\ \Omega$	$\Delta R/R$	-5	5	%
功率损耗/Power dissipation	$T_C = 25^\circ\text{C}$	$P_{25}$		10.0	mW
B 值/B - value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15\text{K}))]$	$B_{25/50}$	3380		K
B 值/B - value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298.15\text{K}))]$	$B_{25/80}$	3468		K
B 值/B - value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298.15\text{K}))]$	$B_{25/100}$	3523		K

# 6H820M08A1E

## 模块 / Module



绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	2.5	kV
模块基板材料 Material of module baseplate			AlSiC	
内部绝缘/Internal isolation	基本绝缘 (class, IEC61140) Basic insulation (class, IEC61140)		ZTA	
爬电距离/Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		9.0 9.0	mm
电气间隙/Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		4.5 4.5	mm
相对电痕指数 Comperative tracking index		CTI	> 200	

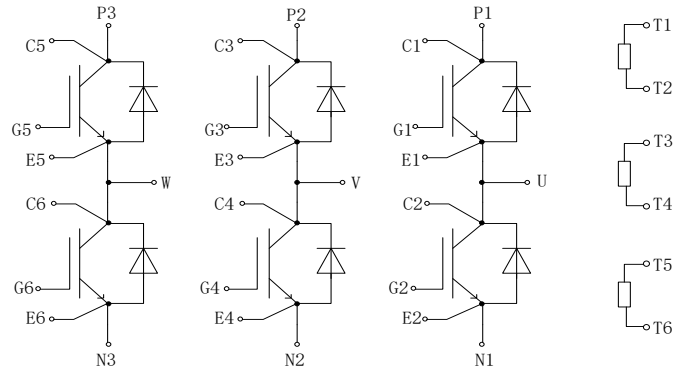
			Min.	Typ.	Max.	
杂散电感, 模块 Stray inductance module		L <sub>sCE</sub>		8.0		nH
储存温度/Storage temperature		T <sub>stg</sub>	-40		125	°C
模块安装的安装扭矩 / Mounting torque for module mounting	螺丝 M4 / Screw M4	M	1.8		2.2	Nm
端子联接扭矩 Terminal connection torque	螺丝 M5 / Screw M5	M	3.0		5.0	Nm
重量/Weight		G		500		g

# 6H820M08A1E

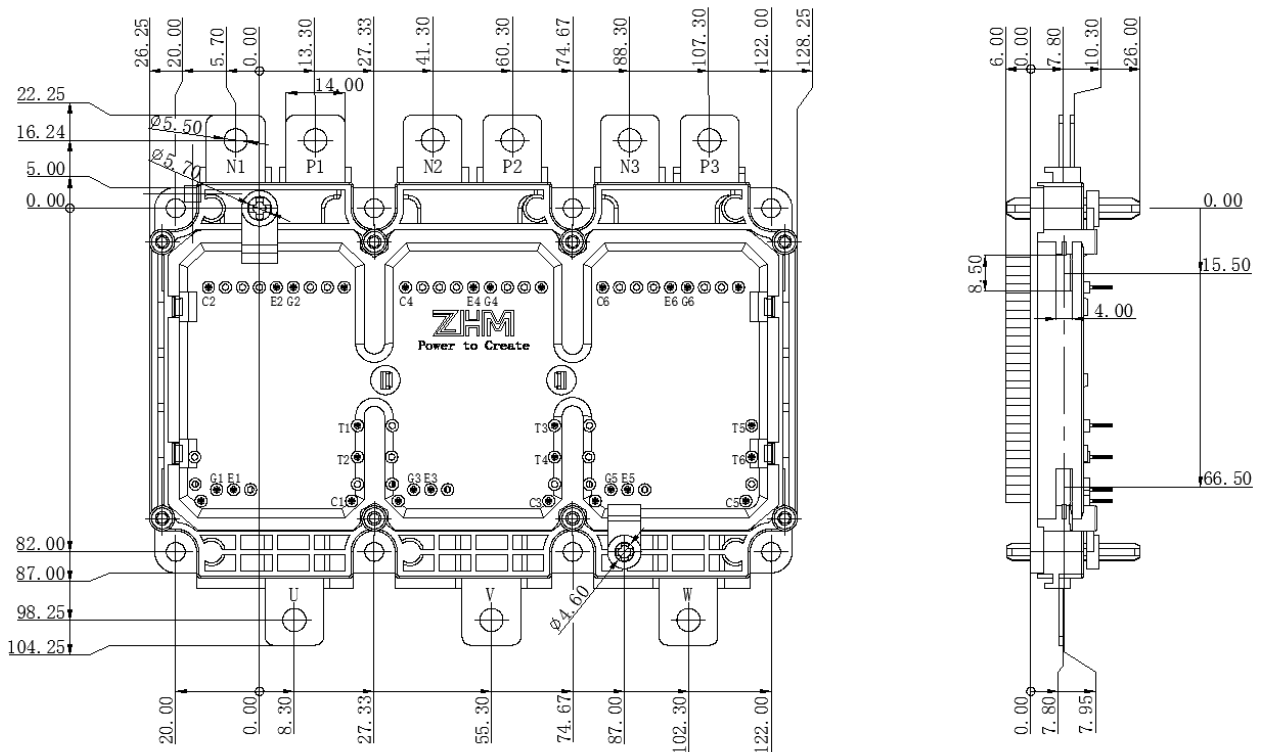
## 封装 / Package



## 接线图 / Circuit Diagram

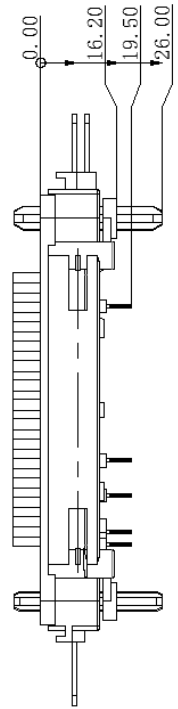
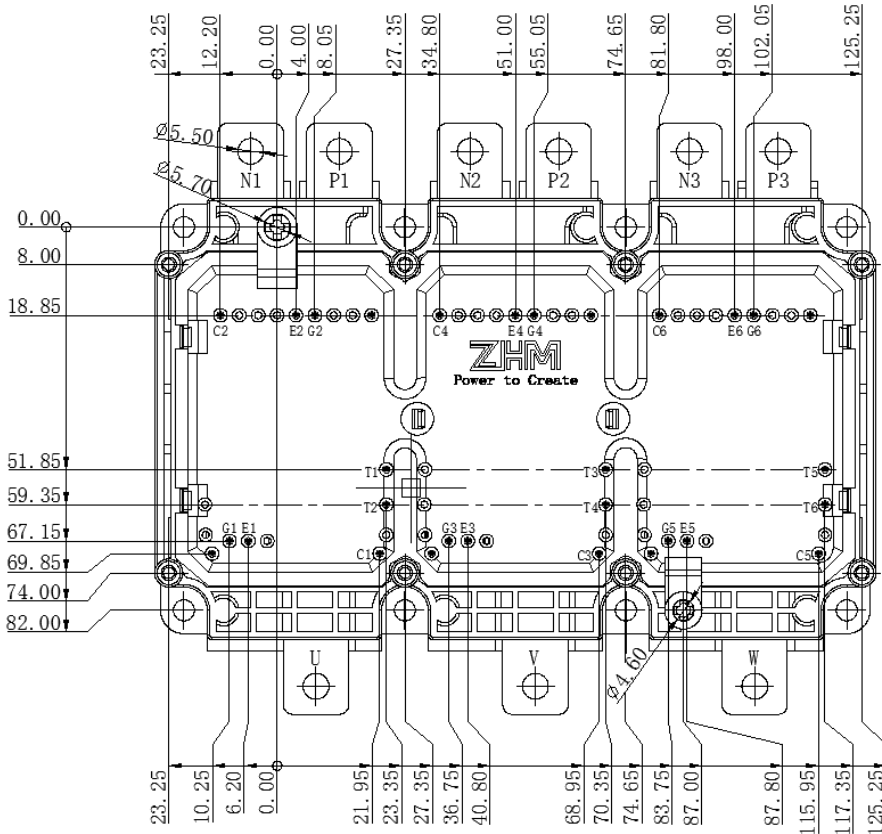


## 封装尺寸 / Package outlines



# 6H820M08A1E

## 封装 / Package

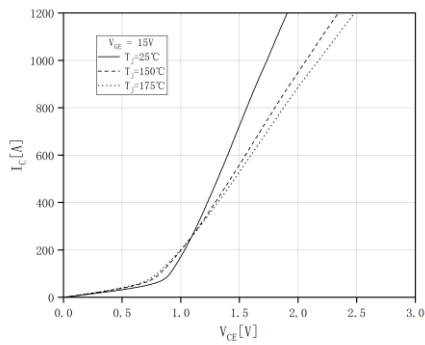


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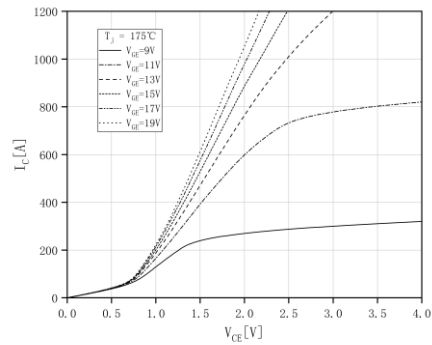
## 性能 / Performance



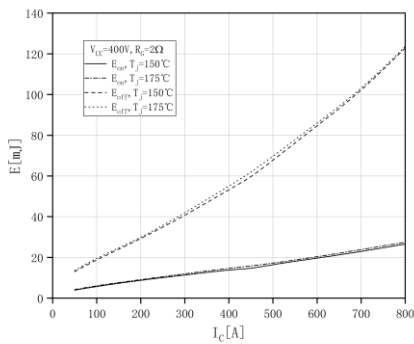
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)



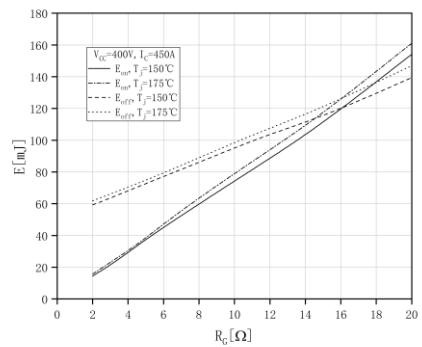
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)



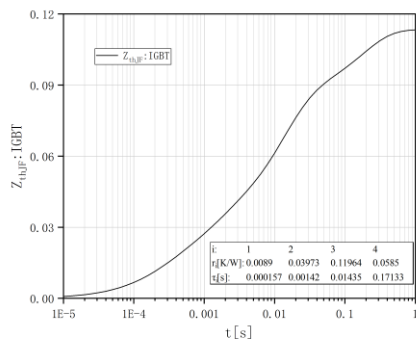
开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)



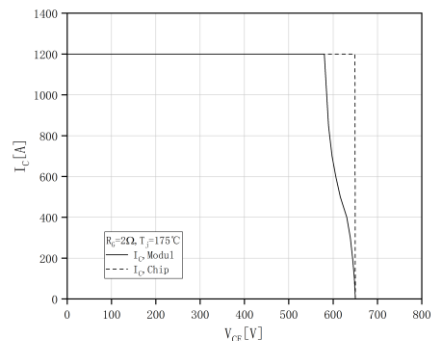
开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)



瞬态热阻抗 IGBT, 逆变器  
transient thermal impedance IGBT, Inverter



反偏安全工作区 IGBT, 逆变器 (RBSOA)  
Reverse bias safe operating area IGBT, Inverter(RBSOA)

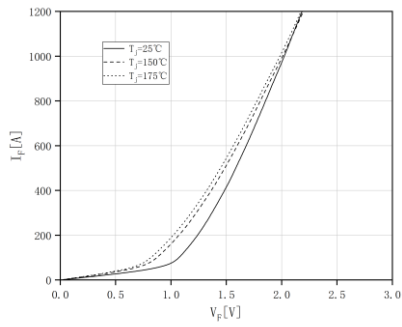


# 6H820M08A1E

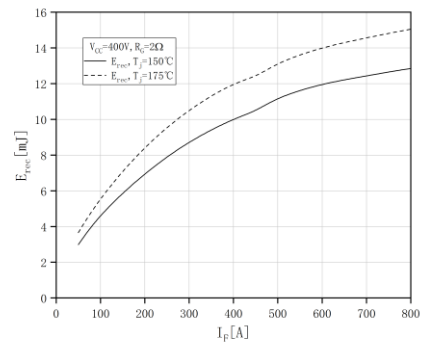
## 性能 / Performance



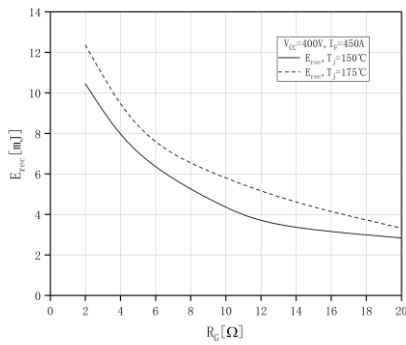
正向偏压特性 二极管,逆变器 (典型)  
forward characteristic of Diode, Inverter(typical)



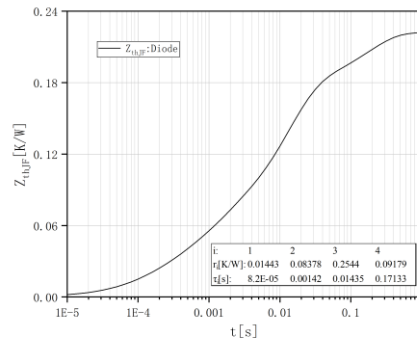
开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter(typical)



开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter(typical)



瞬态热阻抗 二极管, 逆变器  
transient thermal impedance Diode, Inverter





# 6H820M08A1E

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